

Abstract of the Disclosure

A method of removing photoresist material from a semiconductor substrate includes providing a semiconductor substrate having a layer comprised of a low dielectric constant material and a layer comprised of photoresist material disposed over the layer comprised of the low dielectric constant material. The layer comprised of photoresist material is removed with dimethyl sulfoxide (DMSO). The layer of photoresist material is preferably removed by placing the semiconductor substrate in an ultrasonic bath containing DMSO in liquid form. The ultrasonic bath is preferably heated to at least about 50 °C.